

ABSTRACT OF THE DISCLOSURE

In the drying step of the single wafer type substrate cleaning system for cleaning wafers not stored in a cassette, in a sealed cleaning housing, a spin drying treatment is applied to the wafer when the wafer is supported and rotated at high speed while an inert gas for preventing oxidation is supplied to the face of the wafer, and the amount of the inert gas to be supplied to the face of the wafer is larger at the outer peripheral portion of the wafer than that supplied at the center thereof, thereby preventing oxidation on the face of the wafer effectively while optimizing the benefits of the single wafer type cleaning system.